BUK9K89-100E

Dual N-channel TrenchMOS logic level FET

23 July 2012 | Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ > 0.5 V @ 175 °C

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	-	100	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 1		-	-	12.5	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	38	W
Static characteristics FET1 and FET2							
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	75.8	89	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 14; Fig. 15		-	4.2	-	nC

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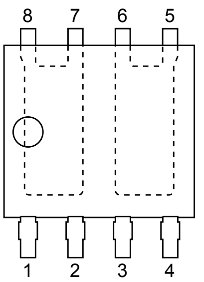
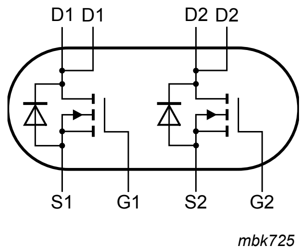
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 LFPAK56D (SOT1205)	
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9K89-100E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; $T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{GS}	gate-source voltage			-10	10	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 5 V; Fig. 1		-	12.5	A
		T_{mb} = 100 °C; V_{GS} = 5 V; Fig. 1		-	8.9	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; Fig. 4		-	50	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	38	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode FET1 and FET2						
I_S	source current	T_{mb} = 25 °C		-	12.5	A

Symbol	Parameter	Conditions		Min	Max	Unit
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	50	A
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 14$ A; $V_{sup} \leq 100$ V; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; Fig. 3	[1][2]	-	19	mJ

[1] Refer to application note AN10273 for further information
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

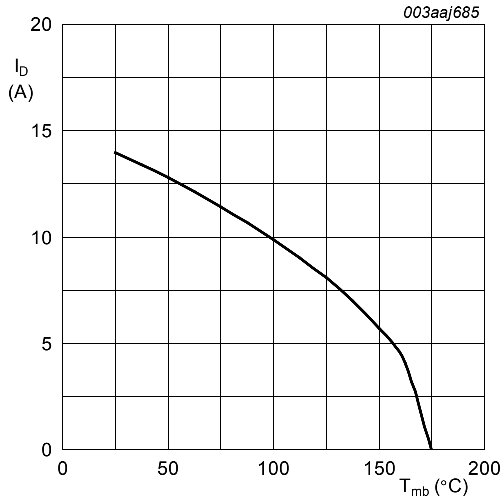


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

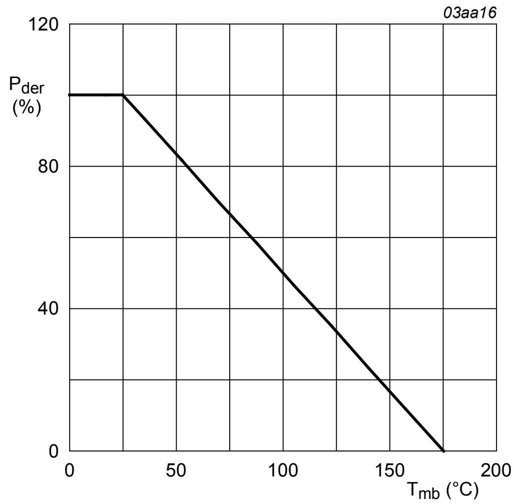


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

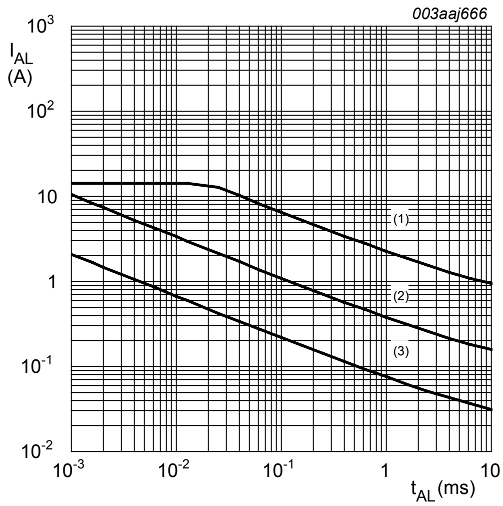


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

(1) Single-pulse; $T_j = 25\,°C$.
(2) Single-pulse; $T_j = 175\,°C$.
(3) Repetitive.

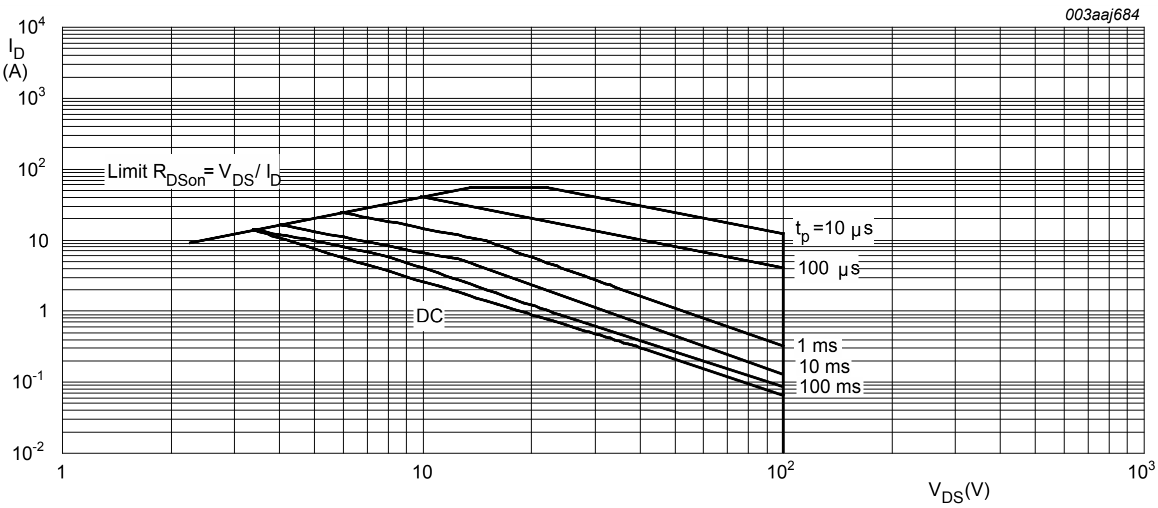


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25\,°C$; I_{DM} is single pulse

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	3.96	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	95	-	K/W

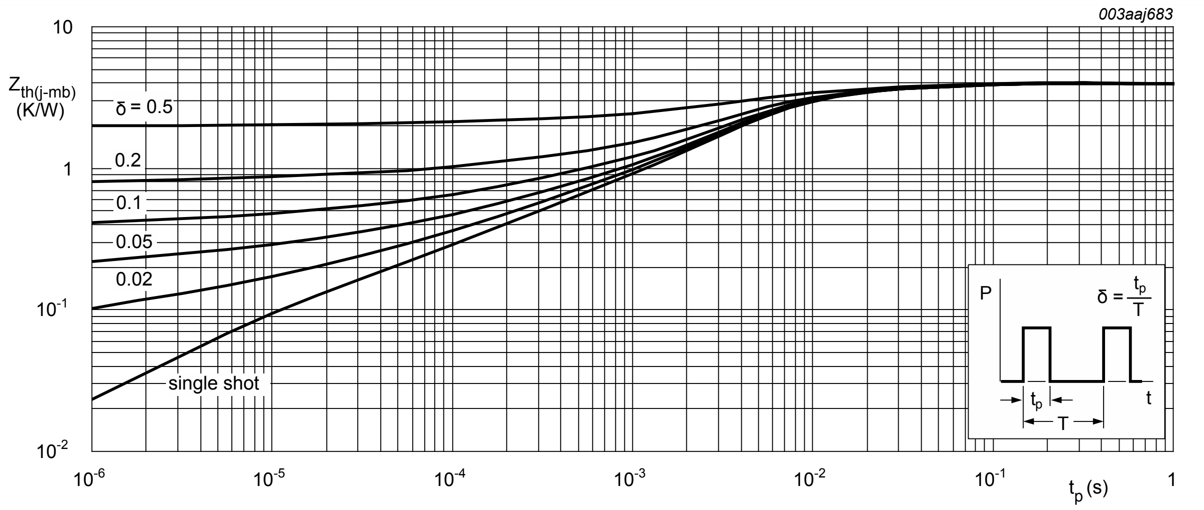


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10; Fig. 11		0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10; Fig. 11		-	-	2.45	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	1	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	75.8	89	mΩ
		V_{GS} = 5 V; I_D = 5 A; T_j = 175 °C; Fig. 12; Fig. 13		-	205.4	241	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	74.9	85	mΩ

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics FET1 and FET2							
$Q_{G(tot)}$	total gate charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 14; Fig. 15		-	16.8	-	nC
Q_{GS}	gate-source charge			-	1.7	-	nC
Q_{GD}	gate-drain charge			-	4.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	1.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	0.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 5 A; V_{DS} = 80 V; Fig. 14; Fig. 15		-	2.5	-	V
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	831	1108	pF
C_{oss}	output capacitance			-	81	97	pF
C_{rss}	reverse transfer capacitance			-	59	81	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 80 V; R_L = 16 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C; I_D = 5 A		-	3.6	-	ns
t_r	rise time			-	5.8	-	ns
$t_{d(off)}$	turn-off delay time	V_{DS} = 80 V; R_L = 16 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; I_D = 18 A; T_j = 25 °C; I_D = 5 A		-	22.1	-	ns
t_f	fall time			-	12.1	-	ns
Source-drain diode FET1 and FET2							
V_{SD}	source-drain voltage	I_S = 5 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V; T_j = 25 °C		-	29.9	-	ns
Q_r	recovered charge			-	39.9	-	nC

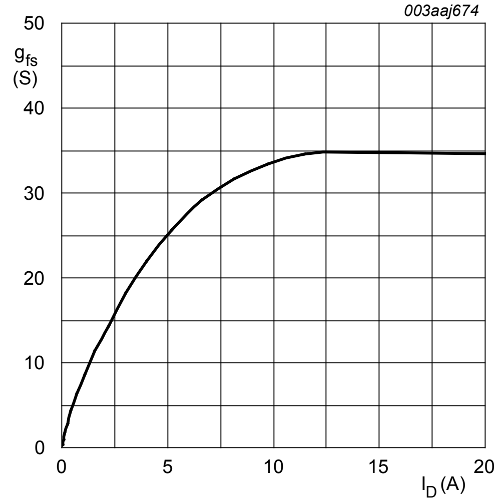


Fig. 6. Forward transconductance as a function of drain current; typical values

$T_j = 25\,°C; V_{DS} = 15\,V$

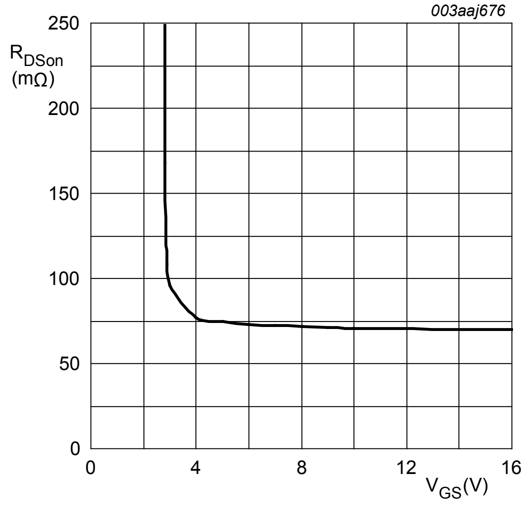


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\,°C;\ I_D = 5\,A$

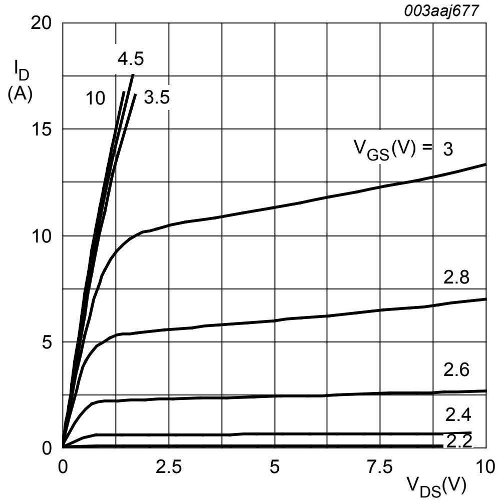


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\,°C$

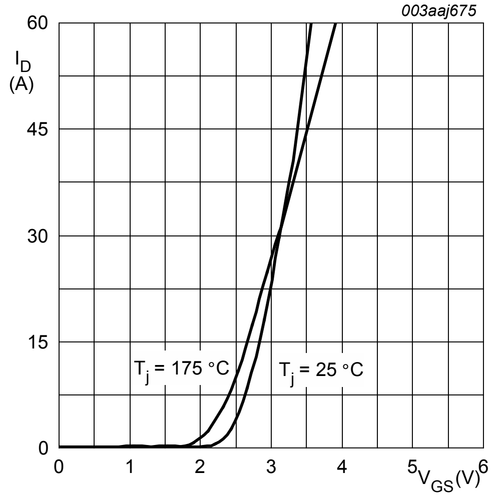


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} > I_D \times R_{DSon}$

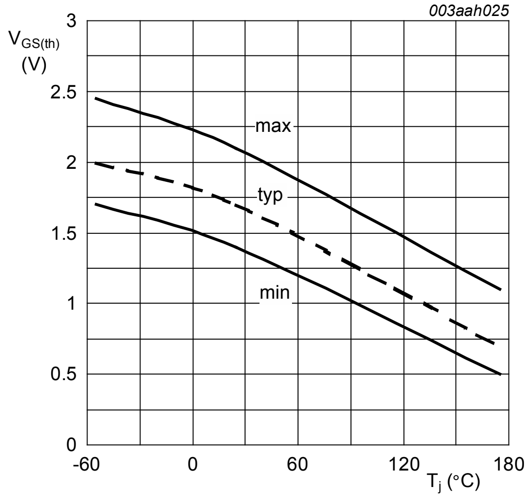


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$

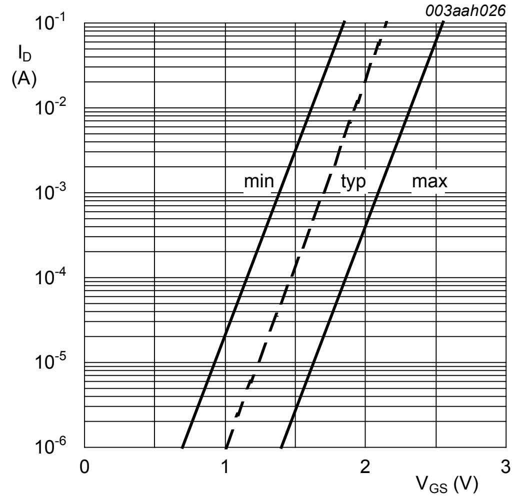


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C$; $V_{DS} = 5V$

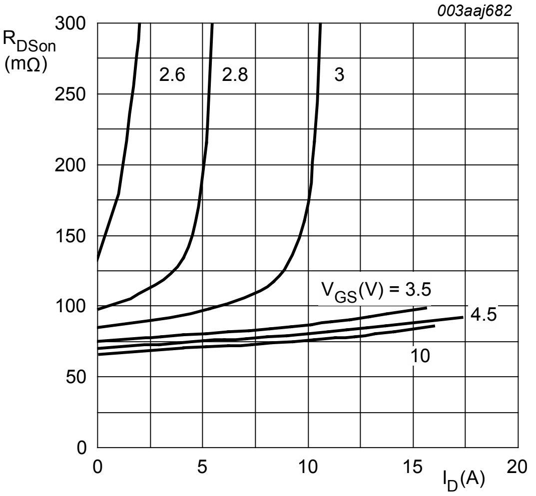


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\,°C$

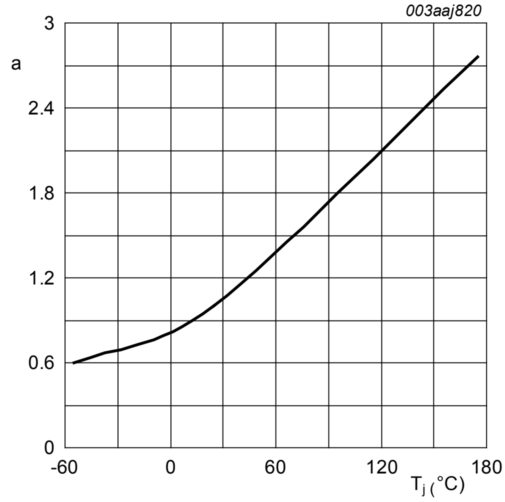


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

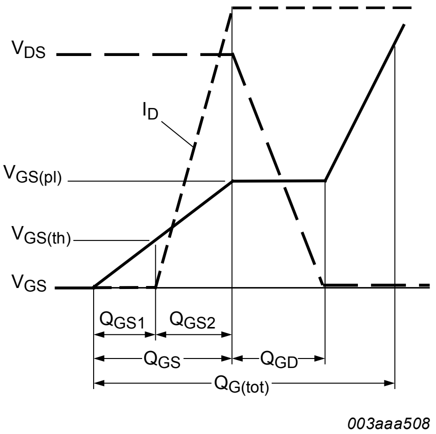


Fig. 14. Gate charge waveform definitions

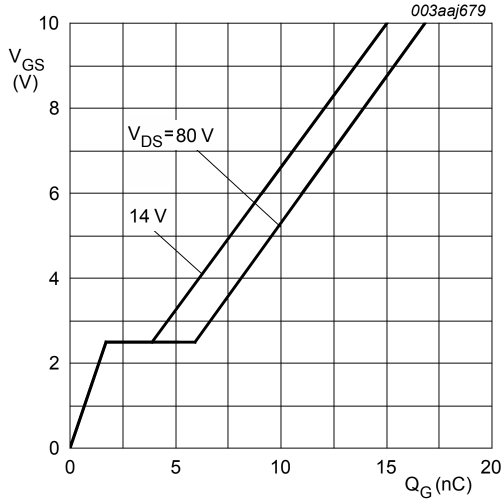


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\,°C; I_D = 5\,A$

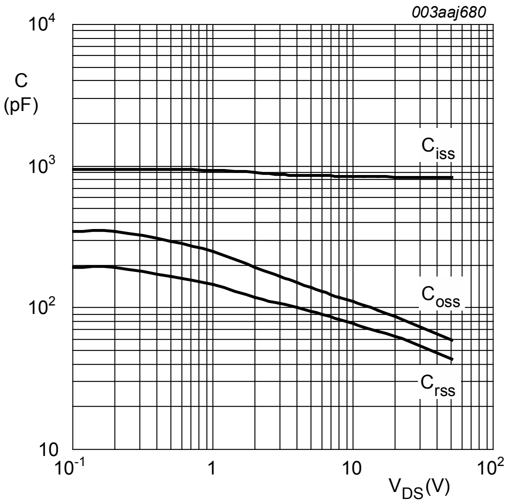


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\,V; f = 1\,MHz$

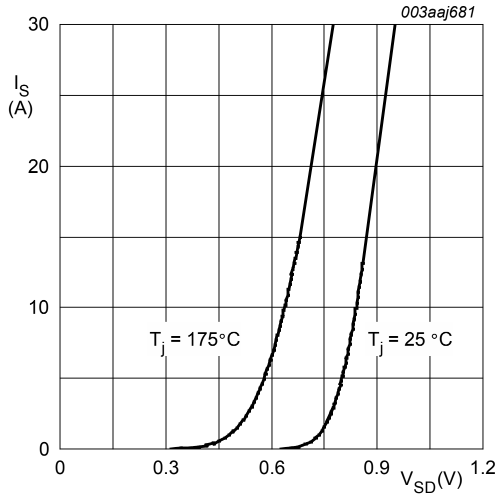
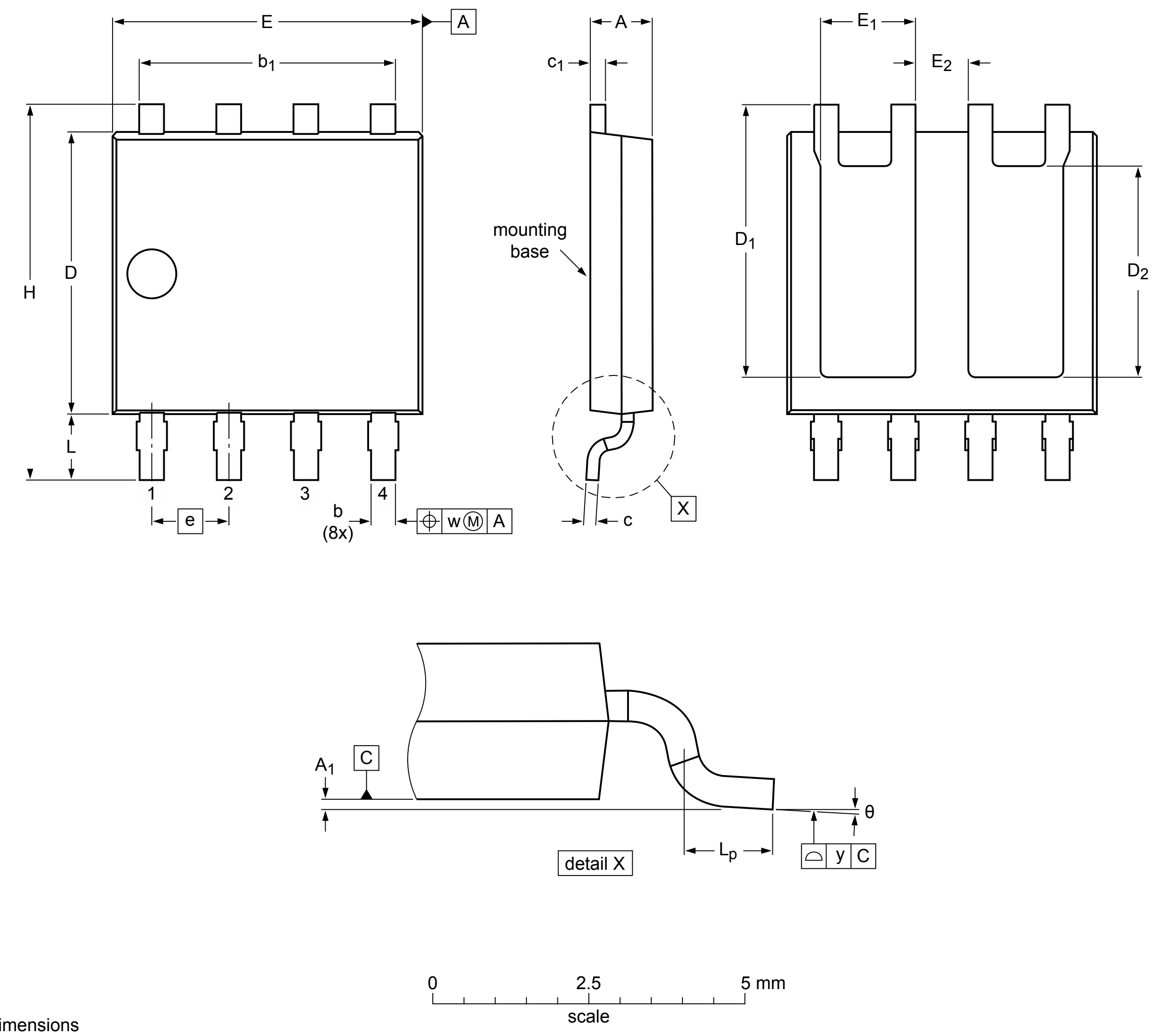


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\,V$

7. Package outline

Plastic single ended surface mounted package (LFPAK56D); 8 leads **SOT1205**



Dimensions

Unit		A	A_1	b	b_1	c	c_1	$D^{(1)}$	$D_1^{(1)}$	D_2 (ref)	$E^{(1)}$	$E_1^{(1)}$	E_2	e	H	L	L_p	w	y	θ
mm	max	1.05	0.1	0.50	4.4	0.25	0.30	4.70	4.8	3.3	5.30	1.6	0.85		6.2	1.3	0.85			8°
	nom													1.27				0.25	0.1	
	min		0.0	0.35	4.1	0.19	0.24	4.45			4.95	1.5			5.9	0.8	0.40			0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1205_po

Outline version	References IEC	References JEDEC	References JEITA		European projection	Issue date
SOT1205						~~11-12-07~~ 12-02-28

Fig. 18. LFPAK56D (SOT1205)

8. Legal information

8.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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